2814

Attorney/Docket No. (formerly TS01-1379)
2001-1379 / 24061.421
Customer No. 42717

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re application of: Yee-Chia Yeo, et al.	§	Group Art Unit: 2814
Serial No. 10/068,928	§	Examiner: Theresa T. Doan
Filed: February 7, 2002	§	
For: MOSFET Device with a Strained Channel	§	

INFORMATION DISCLOSURE STATEMENT

Mail Stop Amendment
Commissioner For Patents
P.O. Box 1450
Alexandria, VA 22313-1450

Dear Sir:

In compliance with the duty of disclosure under 37 CFR §1.56, and in accordance with the practice under 37 CFR §1.97 and §1.98, the Examiner's attention is directed to the documents listed on the enclosed modified Form PTO-1449. No inference should be made that the cited references are in fact material, are in fact prior art, or that no better art exists. The cited patents are listed in numerical order and are not in any order based on their pertinence.

This Information Disclosure Statement is being filed more than three months after the United States filing date and after the mailing date of the first Office Action on the merits, but before the mailing date of a Final Action under §1.113 or Notice of Allowance under §1.311 (37 CFR §1.97(c)).

Accompanying this transmittal is the $180.00 fee set forth in 37 CFR §1.17(p) for submission of an Information Disclosure Statement under §1.97(c).

The Commissioner is hereby authorized to charge any additional fees which may be required or credit any overpayment to Deposit Account 08-1394.

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It is respectfully requested that the above information be considered by the Examiner and that a copy of the enclosed Form PTO-1449 be returned indicating that such information has been considered.

Respectfully submitted,

Wei Wei Jeang
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Date: Oct. 25, 2004
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R-89304.1

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I hereby certify that this correspondence is being deposited with the United States Postal Service as first class mail in an envelope addressed to Commissioner For Patents, P.O. Box 1450, Alexandria, VA 22313-1450 on 10-25-04

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In place of PTO-1449 Form	U. S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE			*Complete if Known*	
INFORMATION DISCLOSURE STATEMENT BY APPLICANT *(use as many sheets as necessary)*				Application Number	10/068,928
				Filing Date	February 7, 2002
				Applicant(s)	Yee-Chia Yeo, et al.
				Art Unit	2814
				Examiner Name	Theresa T. Doan
SHEET	1	OF	1	Attorney Docket Number	(formerly TS01-1379) 2001-1379 / 24061.421

U. S. PATENT DOCUMENTS				
Examiner's Initials	Cite No.	Document Number	Publication Date MM-DD-YYYY	Name of Patentee or Applicant of Cited Document

FOREIGN PATENT DOCUMENTS					
Examiner's Initials	Cite No.	Foreign Patent Document (Country Code – Number – Kind)	Publication Date MM-DD-YYYY	Patentee or Applicant of Cited Document	Translation Y/N

NON-PATENT LITERATURE DOCUMENTS		
Examiner's Initials	Cite No.	Include name of the author (in CAPITAL LETTERS), title of the article, title of the item, date, page(s), volume-issue number(s), publisher, city/country where published
	AA	YANG-KYU CHOI ET AL., *"Ultrathin-Body SOI MOSFET for Deep-Sub-Tenth Micron Era"*, IEEE Electron Device Letters, Vol. 21, No. 5, May 2000, pps. 254-255.
	AB	YANG-KYU CHOI ET AL., *"30nm Ultra-Thin-Body SOI MOSFET with Selectively Deposited Ge Raised S/D"*, Device Research Conference, Denver, CO., June 2000, pps. 23-24.
	AC	Hon-Sum Wong ET AL. *"Three-Dimensional 'Atomistic' Simulation of Discrete Random Dopant Distribution Effects in Sub-0.1 um MOSFET's"* , International Electron Device Meeting Tech. Digest, December 1993, pps. 705-708.
	AD	L.-J. HUANG ET AL, *"Carrier Mobility Enhancement in Strained Si-On-Insulator Fabricated by Wafer Bonding"*, 2001 Symposium on VLSI Technology Digest of Technical Papers, Kyoto, Japan, June 2001, pps. 57-58.
	AE	KERN (KEN) RIM ET AL., *"Fabrication and Analysis of Deep Submicron Strained-Si N-MOSFET'S"*, IEEE Transactions on Electron Devices, Vol. 47, No. 7, July 2000, pps. 1406-1415.
	AF	MICHAEL I. CURRENT ET AL., *"Atomic-layer Cleaving with Si_x Ge_y Strain Layers for Fabrication of Si and Ge-rich Device Layers"*, 2001 IEEE International SOI Conference, October 2001, pps. 11-12.

Examiner Signature		Date Considered	

EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include a copy of this form with next communication to applicant.